NTNS3A65PZ

Small Signal MOSFET

−20 V, −281 mA, Single P−Channel, SOT−883 (XDFN3) 1.0 x 0.6 x 0.4 mm Package

Features

- Single P−Channel MOSFET
- Ultra Low Profile SOT−883 (XDFN3) 1.0 x 0.6 x 0.4 mm for Extremely Thin Environments Such as Portable Electronics
- Low $R_{DS(on)}$ Solution in the Ultra Small 1.0 x 0.6 mm Package
- 1.5 V Gate Drive
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- High Side Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Solutions

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−20	V
Gate−to−Source Voltage			V_{GS}	±8	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	−281	mA
		T_A = 85°C		−202	
	t ≤ 5 s	T_A = 25°C		−332	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	155	mW
	t ≤ 5 s			218	
Pulsed Drain Current	t_p = 10 μs		I_{DM}	−842	mA
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode) (Note 2)			I_S	−130	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface−mounted on FR4 board using the minimum recommended pad size, or 2 mm^2, 1 oz Cu.
2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%

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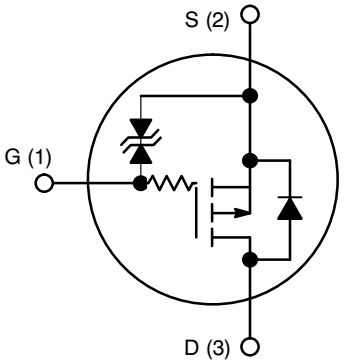
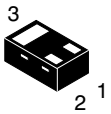
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D Max
−20 V	1.3 Ω @ −4.5 V	−281 mA
	2.0 Ω @ −2.5 V	
	3.4 Ω @ −1.8 V	
	4.5 Ω @ −1.5 V	

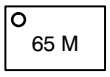
P−CHANNEL MOSFET





SOT−883 (XDFN3)
CASE 506CB

MARKING DIAGRAM



65 = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NTNS3A65PZT5G	SOT−883 (Pb−Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	804	°C/W
Junction−to−Ambient − t ≤ 5 s (Note 3)	$R_{\theta JA}$	574	

3. Surface−mounted on FR4 board using the minimum recommended pad size, or 2 mm^2, 1 oz Cu.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA	−20			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = −250 μA, ref to 25°C		11		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −20 V, T_J = 25°C			−1	μA
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±5 V			±10	μA
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA	−0.4		−1.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.2		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = −4.5 V, I_D = −200 mA		0.9	1.3	Ω
		V_{GS} = −2.5 V, I_D = −100 mA		1.3	2.0	
		V_{GS} = −1.8 V, I_D = −50 mA		1.8	3.4	
		V_{GS}= −1.5 V, I_D = −10 mA		2.3	4.5	Ω
Forward Transconductance	g_{FS}	V_{DS} = −5 V, I_D = −200 mA		0.58		S
Source−Drain Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −100 mA		−0.8	−1.2	V
CHARGES & CAPACITANCES						
Input Capacitance	C_{ISS}	V_{GS} = 0 V, freq = 1 MHz, V_{DS} = −10 V		44		pF
Output Capacitance	C_{OSS}			6.7		
Reverse Transfer Capacitance	C_{RSS}			5.5		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −4.5 V, V_{DS} = −10 V; I_D = −200 mA		1.1		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.1		
Gate−to−Source Charge	Q_{GS}			0.2		
Gate−to−Drain Charge	Q_{GD}			0.2		
SWITCHING CHARACTERISTICS, V_{GS} = 4.5 V (Note 4)						
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −4.5 V, V_{DD} = −10 V, I_D = −200 mA, R_G = 2 Ω		18		ns
Rise Time	t_r			32		
Turn−Off Delay Time	$t_{d(OFF)}$			178		
Fall Time	t_f			84		

4. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

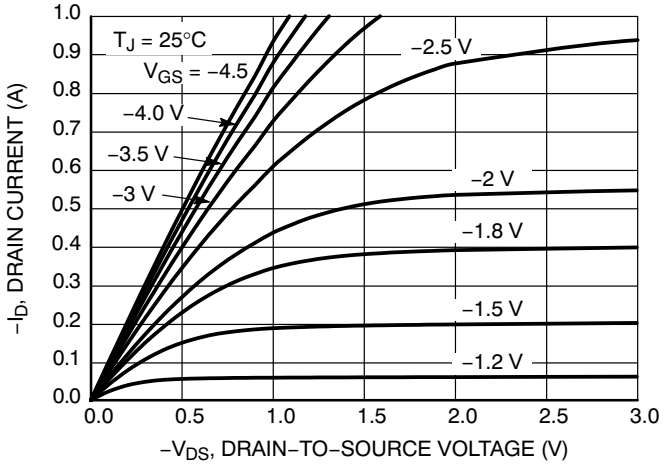


Figure 1. On−Region Characteristics

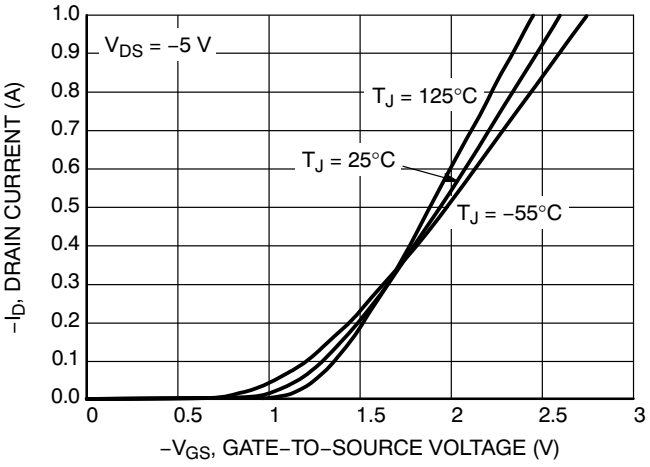


Figure 2. Transfer Characteristics

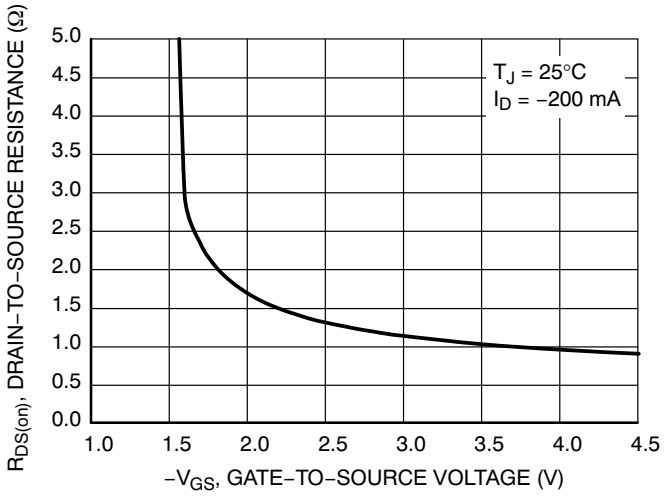


Figure 3. On−Resistance vs. Gate Voltage

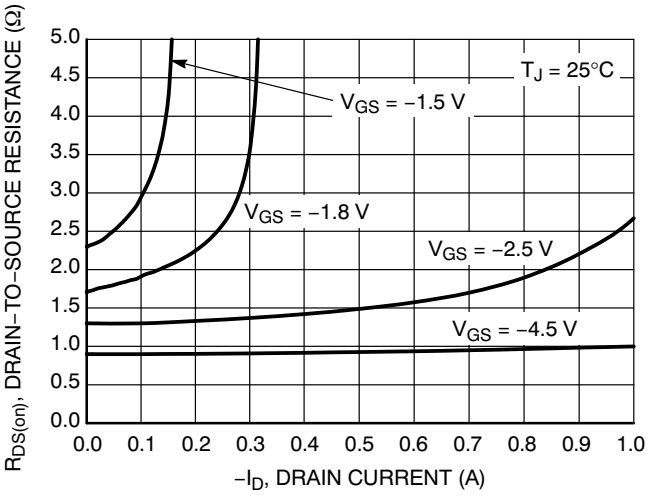


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

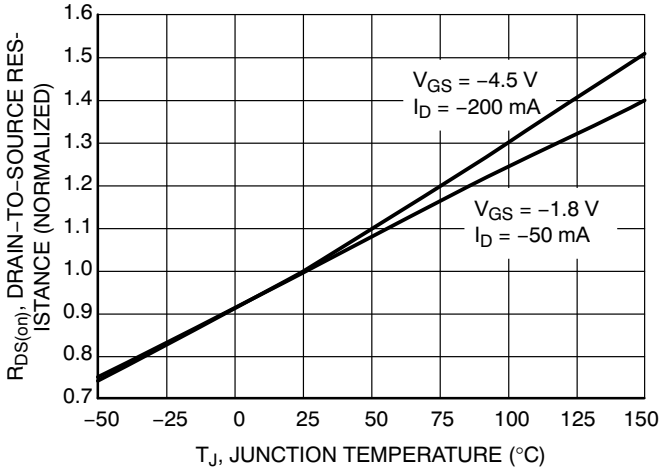


Figure 5. On−Resistance Variation with Temperature

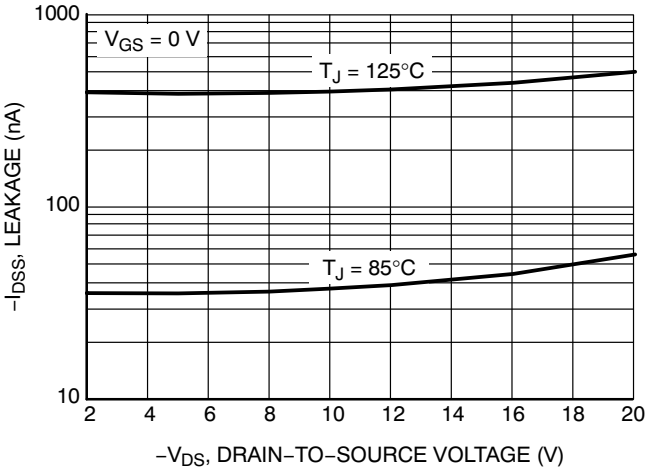


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

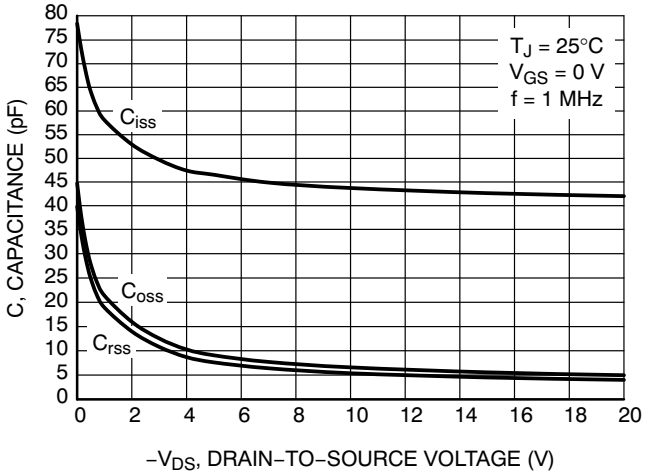


Figure 7. Capacitance Variation

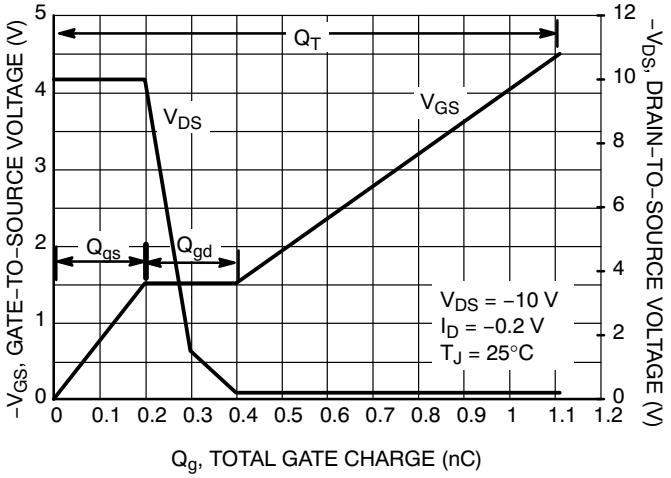


Figure 8. Gate−to−Source Voltage vs. Total Charge

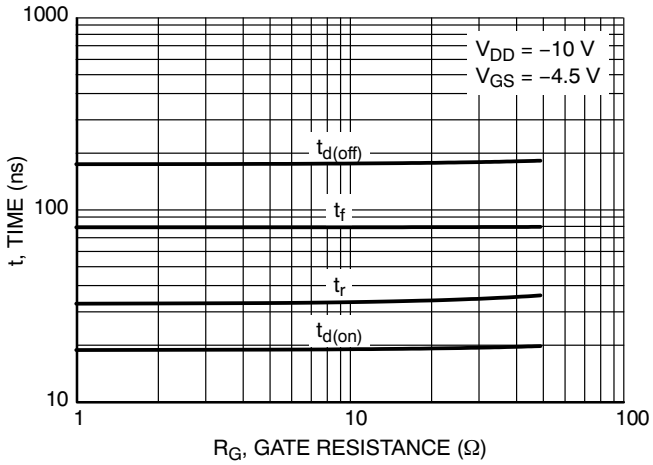


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

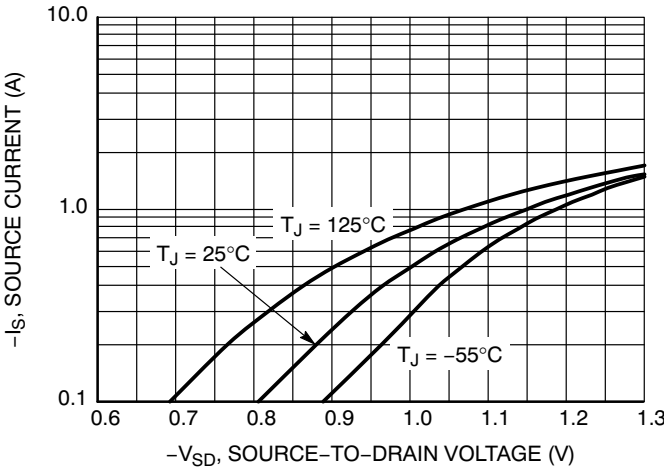


Figure 10. Diode Forward Voltage vs. Current

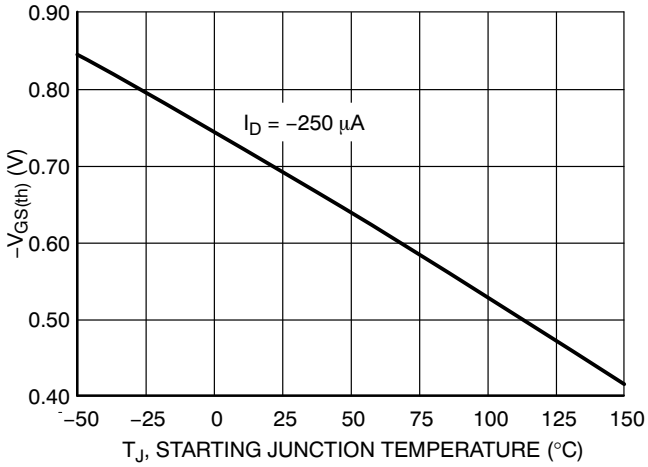


Figure 11. Threshold Voltage

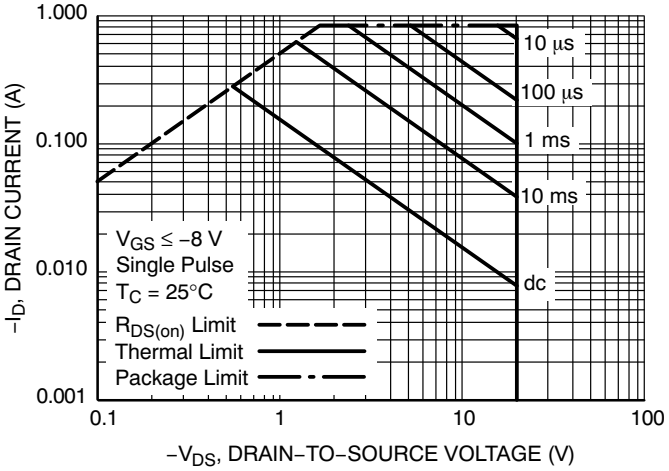


Figure 12. Maximum Rated Forward Biased Safe Operating Area

TYPICAL CHARACTERISTICS

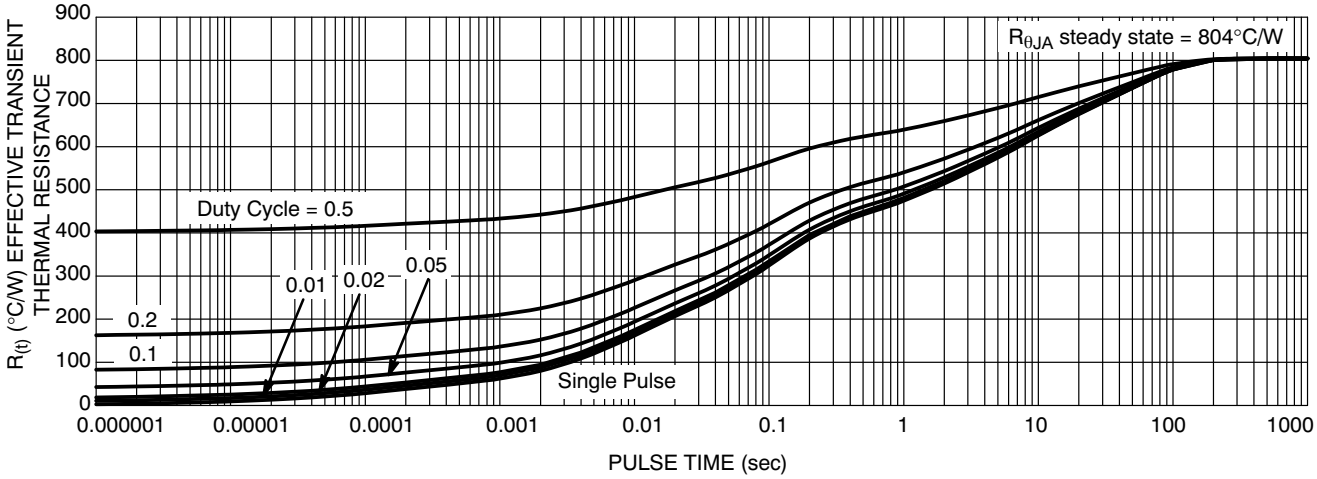
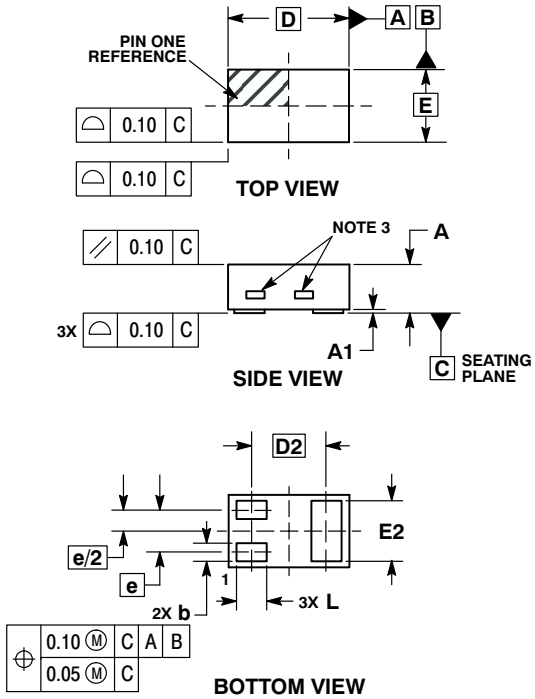


Figure 13. Thermal Response

NTNS3A65PZ

PACKAGE DIMENSIONS

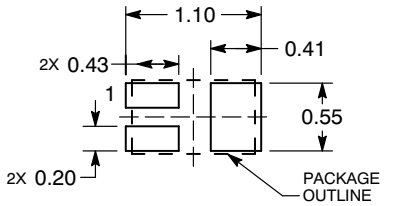
SOT−883 (XDFN3), 1.0x0.6, 0.35P
CASE 506CB
ISSUE A



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. EXPOSED COPPER ALLOWED AS SHOWN.

	MILLIMETERS	
DIM	MIN	MAX
A	0.340	0.440
A1	0.000	0.030
b	0.075	0.200
D	0.950	1.075
D2	0.620 BSC	
e	0.350 BSC	
E	0.550	0.675
E2	0.425	0.550
L	0.170	0.300

RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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